TAN 350

350 Watts, 50 Volts, Pulsed
Avionics 960 – 1215 MHz

GENERAL DESCRIPTION

The **TAN350** is a high power COMMON BASE bipolar transistor. It is designed for pulsed systems in the frequency band 960-1215 MHz. The device has gold thin-film metallization and diffused ballasting for proven highest MTTF. The transistor includes input and output prematch for broadband capability. Low thermal resistance package reduces junction temperature, extends life.

ABSOLUTE MAXIMUM RATINGS

Power Dissipation

Device Dissipation @25°C (P_d) 1450 W (At rated pulse condition)

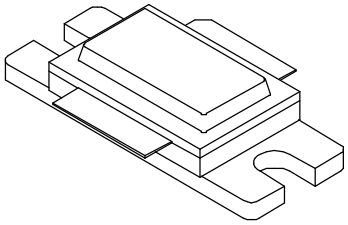
Voltage and Current

Collector to Base Voltage (BV_{ces}) 65 V
Emitter to Base Voltage (BV_{ebo}) 2.0 V
Collector Current (I_c) 40 A

Temperatures

Storage Temperature -65 to +200 °C
Operating Junction Temperature +230 °C

CASE OUTLINE
55ST Style 1



ELECTRICAL CHARACTERISTICS @ 25°C

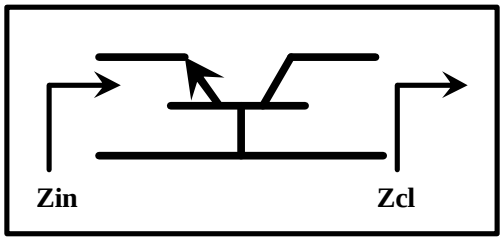
SYMBOL	CHARACTERISTICS	TEST CONDITIONS	MIN	TYP	MAX	UNITS
P_{out}	Power Out	F = 960 – 1215 MHz	350			W
P_{in}	Power Input	V_{CC} = 50 Volts			70	W
P_g	Power Gain	PW = 10 µsec	7.0	7.5		dB
η_c	Collector Efficiency	DF = 10%	38	40		%
VSWR	Load Mismatch Tolerance	F = 1090 MHz	3:1			

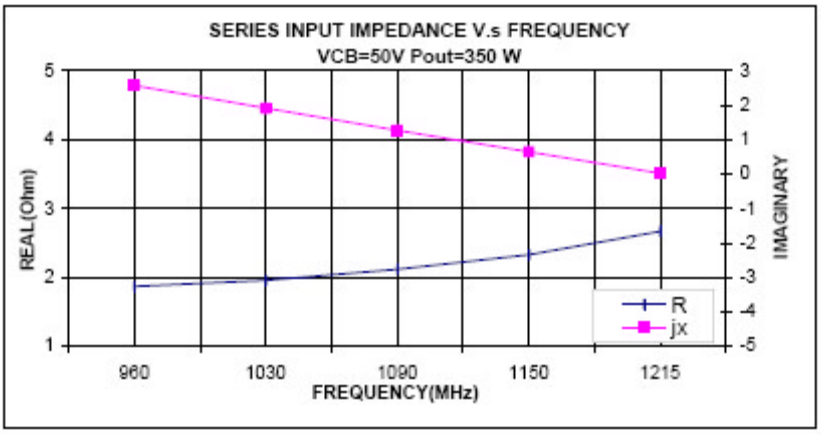
FUNCTIONAL CHARACTERISTICS @ 25°C

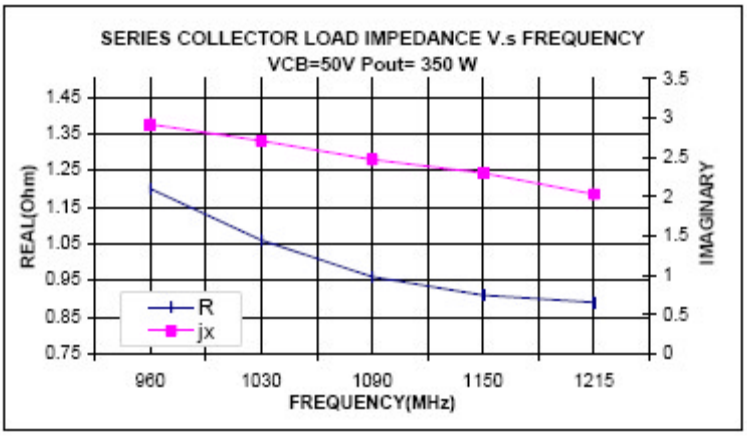
BV_{ebo}	Emitter to Base Breakdown	Ie = 25 mA	2.0			V
BV_{ces}	Collector to Emitter Breakdown	Ic = 50 mA	65			V
h_{FE}	DC – Current Gain	Ic = 1A, Vce = 5V	10			
θjc^2	Thermal Resistance			.12		°C/W

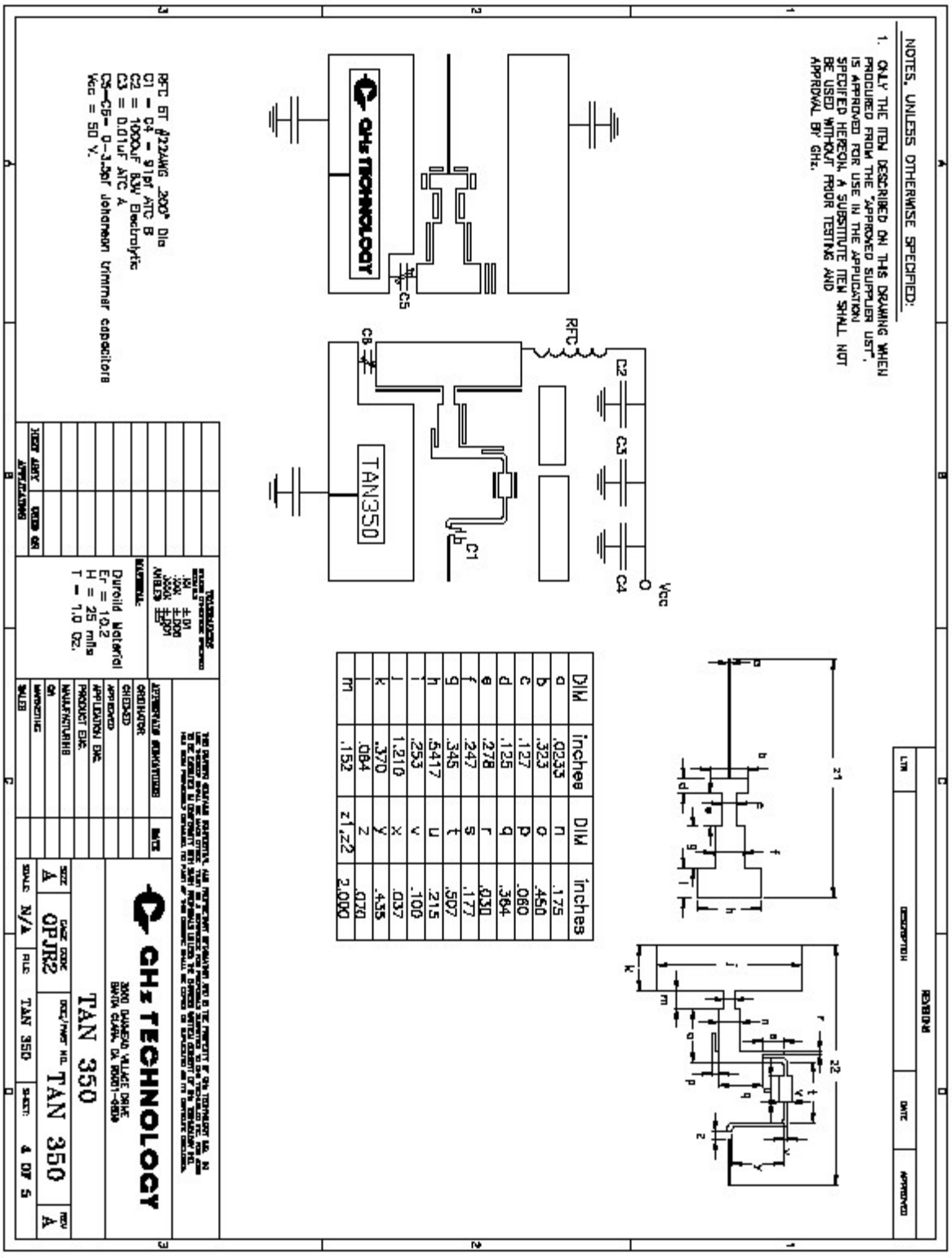
Rev A - Sept. 2005

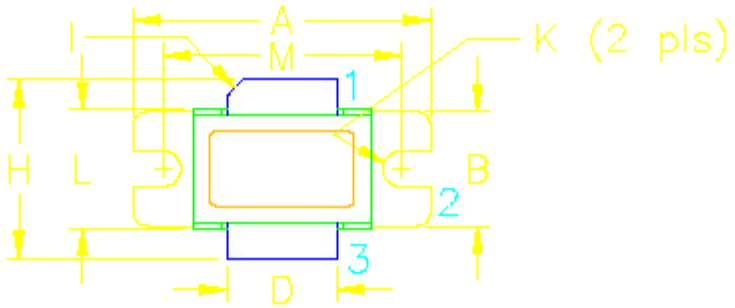
	Zin		ZCL	
Frequency	R	jx	R	jx
960	1.87	2.58	1.2	2.92
1030	1.96	1.92	1.06	2.71
1090	2.12	1.27	0.96	2.47
1150	2.33	0.65	0.91	2.3
1215	2.67	0.03	0.89	2.03

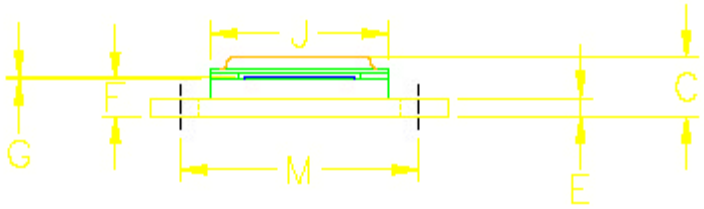








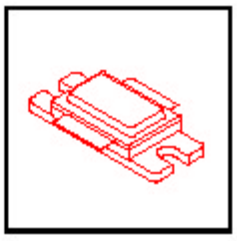




DIM	MILLIMETER	±TOL	INCHES	±TOL
A	25.40	.25	1.000	.010
B	9.78	.25	.385	.010
C	4.00	.19	.142	.007
D	9.40	.13	.370	.005
E	1.53	.13	.060	.005
F	3.18	.13	.125	.005
G	0.08	+.06/-.00	.003	+.002/-.000
H	19.05	0.51	.750	.020
I	45°	5°	45°	5°
J	15.24	.25	.600	.010
K	3.05 DIA	.13	.120 DIA	.005
L	10.15	.13	.400	.005
M	20.32	.25	.800	.010

STYLE 1:
PIN 1 = COLLECTOR
2 = BASE
3 = EMITTER

STYLE 2:
PIN 1 = COLLECTOR
2 = EMITTER
3 = BASE



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